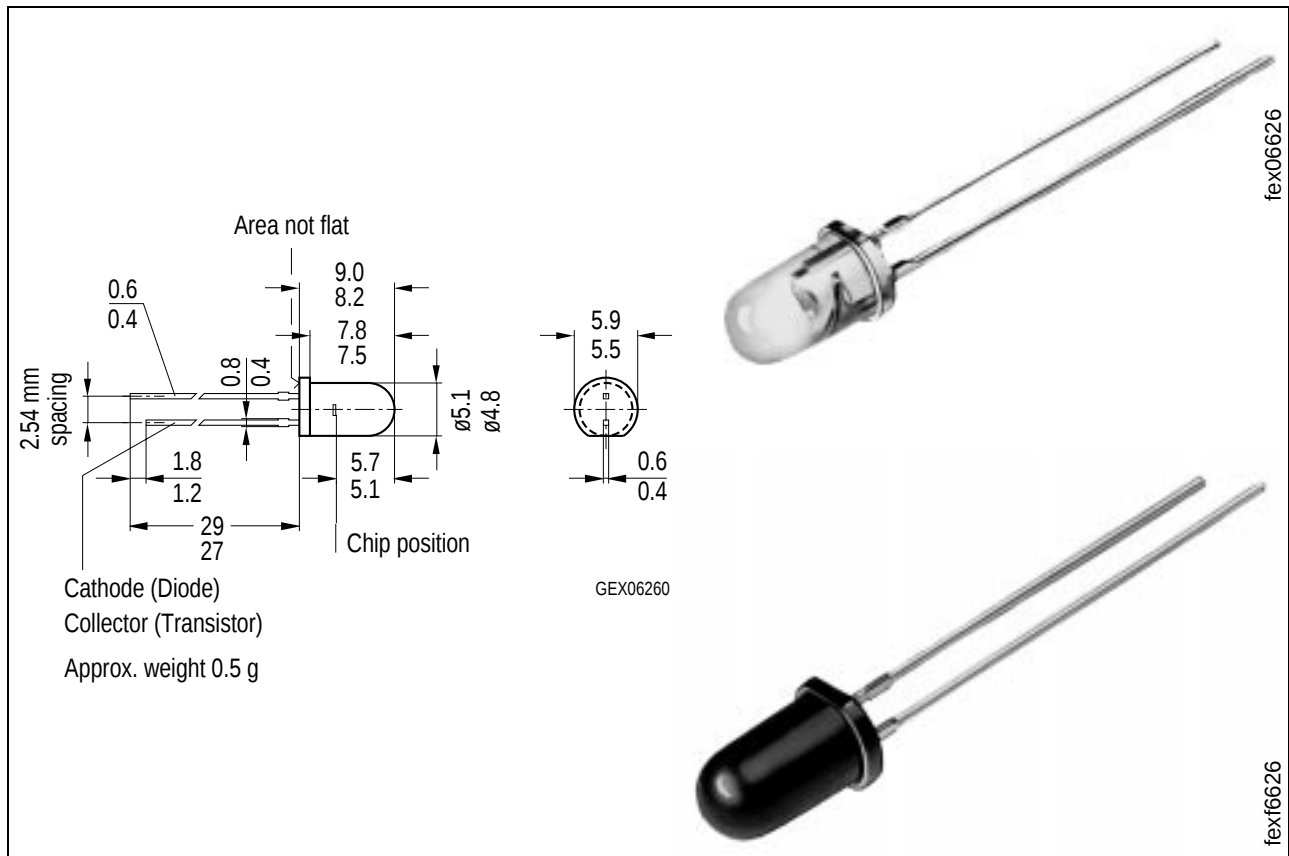


Neu: NPN-Silizium-Fototransistor
New: Silicon NPN Phototransistor

SFH 313
SFH 313 FA



Maße in mm, wenn nicht anders angegeben/Dimensions in mm, unless otherwise specified.

Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 460 nm bis 1080 nm (SFH 313) und bei 880 nm (SFH 313 FA)
- Hohe Linearität
- 5 mm-Plastikbauform

Anwendungen

- Computer-Blitzlichtgeräte
- Lichtschranken für Gleich- und Wechsellichtbetrieb
- Industrieelektronik
- "Messen/Steuern/Regeln"

Features

- Especially suitable for applications from 460 nm to 1080 nm (SFH 313) and of 880 nm (SFH 313 FA)
- High linearity
- 5 mm plastic package

Applications

- Computer-controlled flashes
- Photointerrupters
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code
SFH 313	Q62702-P1667
SFH 313-2	Q62702-P1751
SFH 313-3	Q62702-P1752
SFH 313 FA	Q62702-P1674
SFH 313 FA-2	Q62702-P1753
SFH 313 FA-3	Q62702-P1754

Grenzwerte Maximum Ratings

Bezeichnung Description	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	– 55 ... + 100	°C
Löttemperatur bei Tauchlötung Lötstelle ≥ 2 mm vom Gehäuse, Lötzeit $t \leq 5$ s Dip soldering temperature ≥ 2 mm distance from case bottom, soldering time $t \leq 5$ s	T_S	260	°C
Löttemperatur bei Kolbenlötung Lötstelle ≥ 2 mm vom Gehäuse, Lötzeit $t \leq 3$ s Iron soldering temperature ≥ 2 mm distance from case bottom $t \leq 3$ s	T_S	300	°C
Kollektor-Emitterspannung Collector-emitter voltage	V_{CE}	70	V
Kollektorstrom Collector current	I_C	50	mA
Kollektorspitzenstrom, $\tau < 10 \mu s$ Collector surge current	I_{CS}	100	mA
Emitter-Kollektorspannung Emitter-collector voltage	V_{EC}	7	V
Verlustleistung, $T_A = 25$ °C Total power dissipation	P_{tot}	200	mW
Wärmewiderstand Thermal resistance	R_{thJA}	375	K/W

Kennwerte ($T_A = 25\text{ °C}$, $\lambda = 950\text{ nm}$)

Characteristics

Bezeichnung Description	Symbol Symbol	Wert Value		Einheit Unit
		SFH 313	SFH 313 FA	
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\text{ max}}$	850	870	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\text{ \%}$ von S_{max} Spectral range of sensitivity $S = 10\text{ \%}$ of S_{max}	λ	460 ... 1080	740 ... 1080	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	0.55	0.55	mm ²
Abmessung der Chipfläche Dimensions of chip area	$L \times B$ $L \times W$	1 × 1	1 × 1	mm × mm
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip front to case surface	H	5.1 ... 5.7	5.1 ... 5.7	mm
Halbwinkel Half angle	φ	± 10	± 10	Grad deg.
Kapazität, $V_{\text{CE}} = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ Capacitance	C_{CE}	15	15	pF
Dunkelstrom Dark current $V_{\text{CE}} = 10\text{ V}$, $E = 0$	I_{CEO}	10 (≤ 200)	10 (≤ 200)	nA
Fotostrom Photocurrent $E_e = 0.5\text{ mW/cm}^2$, $V_{\text{CE}} = 5\text{ V}$ $E_v = 1000\text{ lx}$, Normlicht/standard light A, $V_{\text{CE}} = 5\text{ V}$	I_{PCE} I_{PCE}	≥ 2.5 30	≥ 2.5 –	mA mA

Die Fototransistoren werden nach ihrer Fotoempfindlichkeit gruppiert und mit arabischen Ziffern gekennzeichnet.

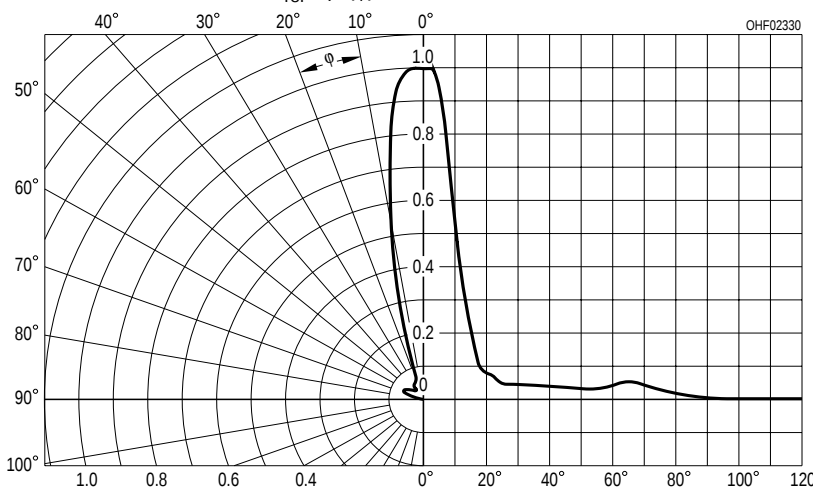
The phototransistors are grouped according to their spectral sensitivity and distinguished by arabian figures.

Bezeichnung Description	Symbol	Wert Value				Einheit Unit
		-1	-2	-3	-4	
Fotostrom, $\lambda = 950 \text{ nm}$ Photocurrent $E_e = 0.5 \text{ mW/cm}^2$, $V_{CE} = 5 \text{ V}$	I_{PCE}	2.5 ... 5	4 ... 8	6.3 ... 12.5	≥ 10	mA
Anstiegszeit/Abfallzeit Rise and fall time $I_C = 1 \text{ mA}$, $V_{CC} = 5 \text{ V}$, $R_L = 1 \text{ k}\Omega$	t_r, t_f	8	10	12	14	μs
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage $I_C = I_{PCEmin}^{1)} \times 0.3$, $E_e = 0.5 \text{ mW/cm}^2$	V_{CEsat}	150	150	150	150	mV

1) I_{PCEmin} ist der minimale Fotostrom der jeweiligen Gruppe

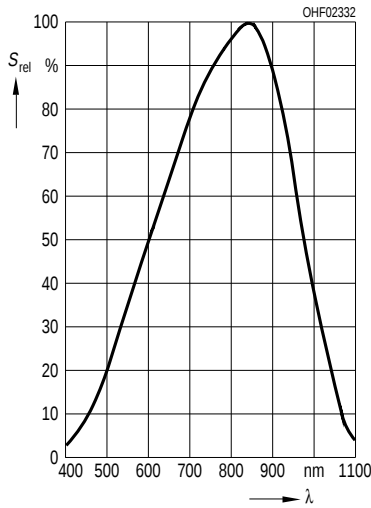
1) I_{PCEmin} is the min. photocurrent of the specified group

Directional characteristics $S_{rel} = f(\varphi)$

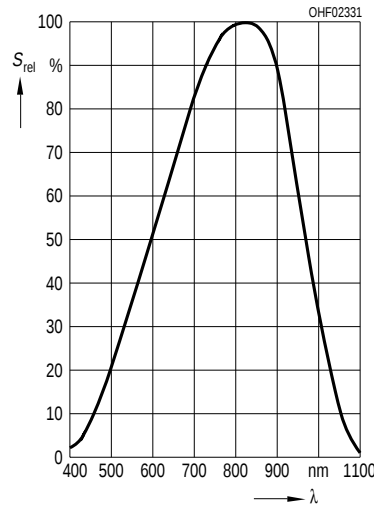


$T_A = 25^\circ\text{C}$, $\lambda = 950\text{ nm}$

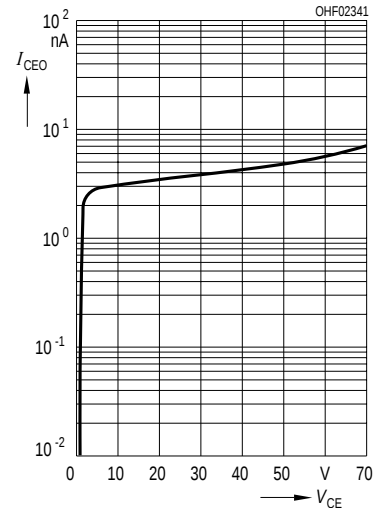
Rel.spectr.sensitivity SFH 313, $S_{\text{rel}} = f(\lambda)$



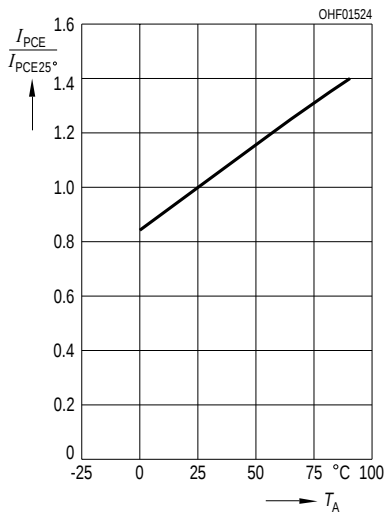
Rel.spectr.sensitivity SFH 313FA, $S_{\text{rel}} = f(\lambda)$



Dark current, $I_{\text{CEO}} = f(V_{\text{CE}})$, $E = 0$

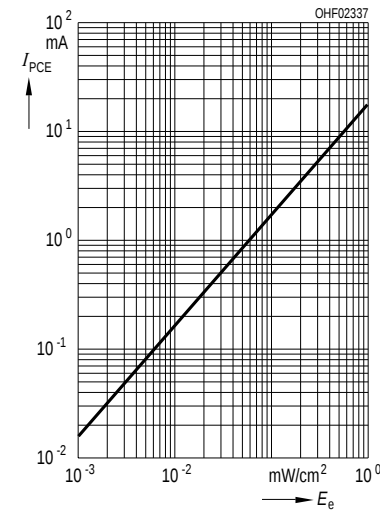


Photocurrent $I_{\text{PCE}} = f(T_A)$,
 $V_{\text{CE}} = 5\text{ V}$, normalized to 25°C



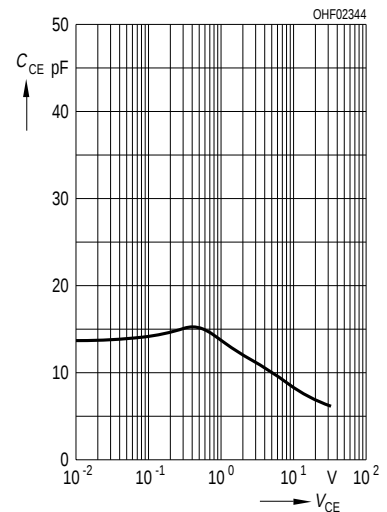
Photocurrent

$I_{\text{PCE}} = f(E_e)$, $V_{\text{CE}} = 5\text{ V}$

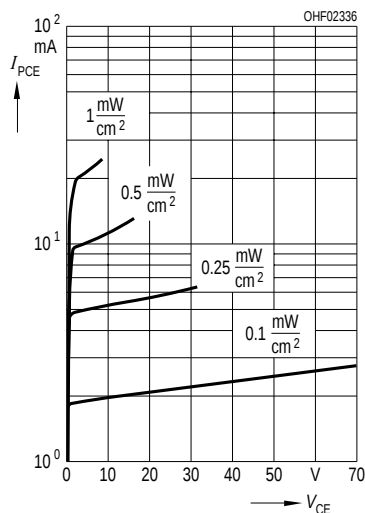


Collector-emitter capacitance

$C_{\text{CE}} = f(V_{\text{CE}})$, $f = 1\text{ MHz}$

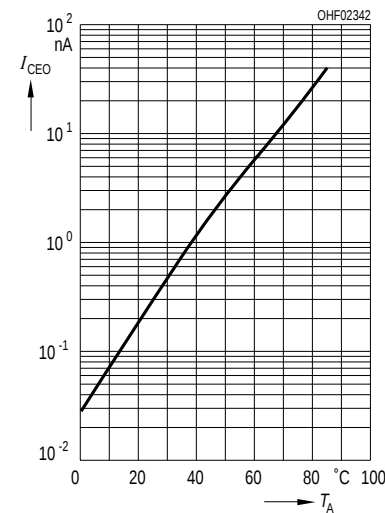


Photocurrent $I_{\text{PCE}} = f(V_{\text{CE}})$
 $E = \text{parameter}$



Dark current

$I_{\text{CEO}} = f(T_A)$, $V_{\text{CE}} = 10\text{ V}$, $E = 0$



Total power dissipation

$P_{\text{tot}} = f(T_A)$

